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INFORMATION DISCLOSURE
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Sheet A1 of

Complete if Known

Application Number	10/772,882
Filing Date	February 5, 2004
First Named Inventor	Saxler
Group Art Unit	2811
Examiner Name	Jerome Jackson, Jr.
Attorney Docket Number	5308-389

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Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
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	21.	Burn et al., "Recessed Gate GaN MODFETS," <i>Solid State Electronics</i> , Vol. 41, No. 2, pp. 247-50 (1997)	
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Examiner Signature

Date Considered

7/10/04

*EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.